IN THE SPECIFICATION

pages 8 and 10

Please replace the paragraph beginning at page 8, line 15, through page 9, line 2, with the following rewritten paragraph:

The baking gas feed line 13 is provided with an activation section 14 disposed thereon for activating the baking gas. The activation section 14 is arranged to activate the baking gas by means of heat, plasma, light, or catalyst, and thus includes, e.g., heating means, plasma generation means, photolyzation means, or catalytic activation means. In this embodiment, the activation section 14 is formed of a heating device configured to heat the baking gas to a temperature for activation, ~~raging~~, ranging e.g., from 500 to 2000°C, and preferably 700 to 1000 °C. The baking gas supplied from the baking gas supply source is heated and thereby activated by the heating device (activation section 14), and this activated baking gas is supplied into the reaction tube 2.

Please replace the paragraph beginning at page 10, line 23, through page 11, line 4, with the following rewritten paragraph:

Next, an explanation will be ~~give~~ given of a heat-processing method, using the heat-processing apparatus 1 described above. This embodiment is exemplified by a method for processing an organosiloxane film. In summary, a coating film of a polysiloxane base solution having an organic functional group is formed by spin coating on a target substrate or semiconductor wafer. Then, the wafer is subjected to a heat process (baking process) to bake the coating film.